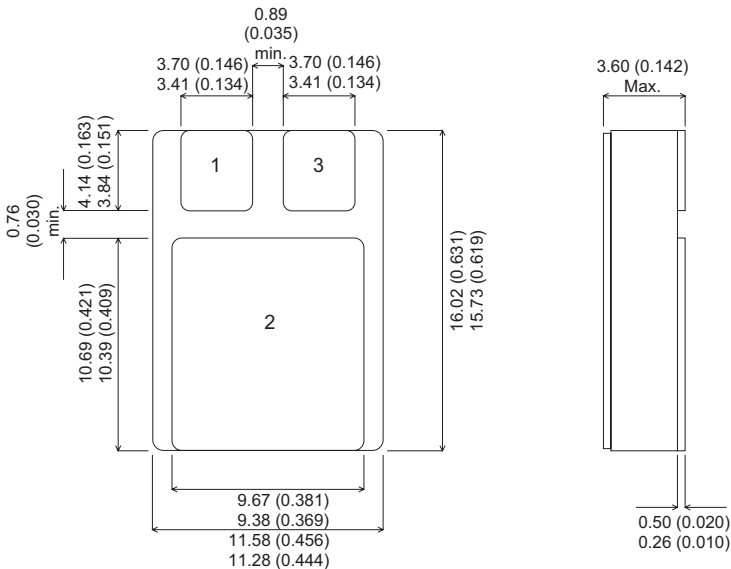


MECHANICAL DATA

Dimensions in mm (inches)



**P-CHANNEL
POWER MOSFET**

V_{DSS} **-100V**
 $I_{D(cont)}$ **-31A**
 $R_{DS(on)}$ **0.060Ω**

FEATURES

- HERMETICALLY SEALED SURFACE MOUNT PACKAGE
- SMALL FOOTPRINT – EFFICIENT USE OF PCB SPACE.
- SIMPLE DRIVE REQUIREMENTS
- LIGHTWEIGHT
- HIGH PACKING DENSITIES

SMD 1 PACKAGE (TO-276AB)

Pad 1 – Source Pad 2 – Drain Pad 3 – Gate

Note: IRF5210SMD also available with pins 1 and 3 reversed.

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{GS}	Gate – Source Voltage	$\pm 20V$
I_D	Continuous Drain Current ($V_{GS} = 0, T_{case} = 25^{\circ}C$)	-31A
I_D	Continuous Drain Current ($V_{GS} = 0, T_{case} = 100^{\circ}C$)	-19A
I_{DM}	Pulsed Drain Current ¹	-124A
P_D	Power Dissipation @ $T_{case} = 25^{\circ}C$	125W
	Linear Derating Factor	1.0W/ $^{\circ}C$
E_{AS}	Single Pulse Avalanche Energy ²	340mJ
dv/dt	Peak Diode Recovery ³	4.0V/ns
T_J, T_{stg}	Operating and Storage Temperature Range	-55 to 150 $^{\circ}C$
T_L	Package Mounting Surface Temperature (for 5 sec)	300 $^{\circ}C$
$R_{\theta JC}$	Thermal Resistance Junction to Case	1.0 $^{\circ}C/W$

- Notes**
- 1) Pulse Test: Pulse Width $\leq 300ms, \delta \leq 2\%$
 - 2) @ $V_{DD} = -25V, L = 1.9mH, Peak I_{AS} = -19A, V_{GS} = -10V, R_G = 25\Omega, Starting T_J = 25^{\circ}C$
 - 3) @ $I_{SD} \leq -19A, di/dt \leq -390A/\mu s, V_{DD} \leq -100V, T_J \leq 150^{\circ}C$

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
STATIC ELECTRICAL RATINGS					
BV_{DSS}	Drain – Source Breakdown Voltage	$V_{GS} = 0$ $I_D = -250\mu\text{A}$	-100		V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	Reference to 25°C $I_D = -1\text{mA}$		-0.11	$\text{V}/^{\circ}\text{C}$
$R_{DS(on)}$	Static Drain – Source On–State Resistance ¹	$V_{GS} = -10\text{V}$ $I_D = -19\text{A}$		0.06	Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = -250\mu\text{A}$	-2.0	-4.0	V
g_{fs}	Forward Transconductance ¹	$V_{DS} = -50\text{V}$ $I_{DS} = -19\text{A}$	10		$\text{S}(\overline{75})$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0$ $V_{DS} = -80\text{V}$ $T_J = 125^{\circ}\text{C}$		-25 -250	μA
I_{GSS}	Forward Gate – Source Leakage	$V_{GS} = -20\text{V}$		-100	nA
I_{GSS}	Reverse Gate – Source Leakage	$V_{GS} = 20\text{V}$		100	
DYNAMIC CHARACTERISTICS					
C_{iss}	Input Capacitance	$V_{GS} = 0$		2700	pF
C_{oss}	Output Capacitance	$V_{DS} = -25\text{V}$		830	
C_{rss}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		470	
Q_g	Total Gate Charge ¹	$V_{GS} = -10\text{V}$ $I_D = -19\text{A}$ $V_{DS} = -80\text{V}$		215	nC
Q_{gs}	Gate – Source Charge ¹	$V_{GS} = -10\text{V}$ $I_D = -19\text{A}$		30	nC
Q_{gd}	Gate – Drain (“Miller”) Charge ¹	$V_{DS} = -80\text{V}$		115	
$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = -50\text{V}$ $V_{GS} = -10\text{V}$ $I_D = -19\text{A}$ $R_G = 2.5\Omega$		28	ns
t_r	Rise Time			150	
$t_{d(off)}$	Turn–Off Delay Time			103	
t_f	Fall Time			116	
SOURCE – DRAIN DIODE CHARACTERISTICS					
I_S	Continuous Source Current			-31	A
I_{SM}	Pulse Source Current ²			-124	
V_{SD}	Diode Forward Voltage	$I_S = -19\text{A}$ $T_J = 25^{\circ}\text{C}$ $V_{GS} = 0$		-1.6	V
t_{rr}	Reverse Recovery Time	$I_F = -19\text{A}$ $T_J = 25^{\circ}\text{C}$		290	ns
Q_{rr}	Reverse Recovery Charge	$d_i / d_t \leq 100\text{A}/\mu\text{s}$ $V_{DD} \leq -50\text{V}$		2.1	μC
t_{on}	Forward Turn–On Time		Negligible		

Notes

- 1) Pulse Test: Pulse Width $\leq 300\text{ms}$, $\delta \leq 2\%$
- 2) Repetitive Rating – Pulse width limited by maximum junction temperature.

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